

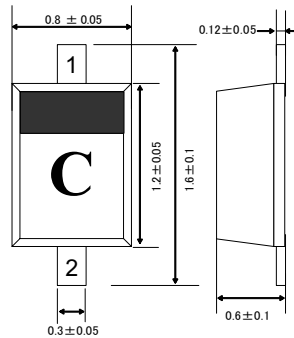
RB521S30

Schottky Barrier Diodes

Features

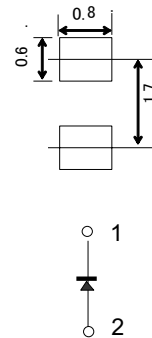
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability
- These are Pb-Free Devices

●External dimensions (Unit : mm)



SOD-523

●Land size figure (Unit : mm)



ORDER INFORMATION

MODEL	PIN-PACKAGE	ORDERING NUMBER	PACKAGE MARKING	PACKAGE OPTION
RB521S30	SOD523	RB521S30-2/TR	C	3000/Tape&Reel

Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	200	mA
Peak forward surge current	I _{FSM}	1	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.5	V	I _F =200mA
Reverse current	I _R			30	μA	V _R =10V

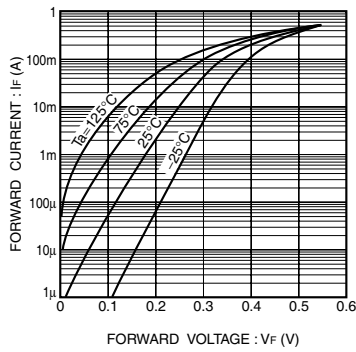
Typical Characteristics
RB521S30


Fig. 1 Forward characteristics

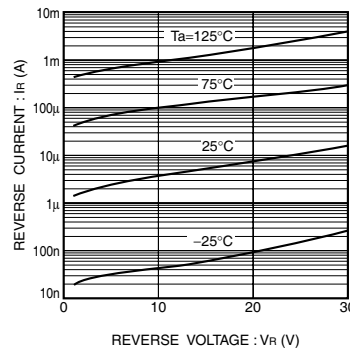


Fig. 2 Reverse characteristics

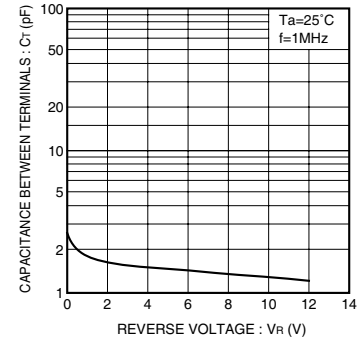


Fig. 3 Capacitance between terminals characteristics

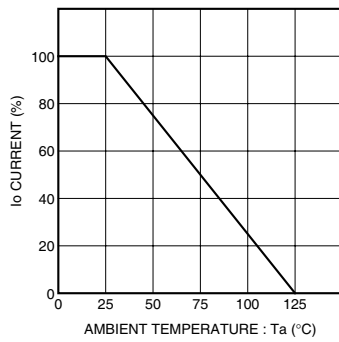


Fig. 4 Derating curve (mounting on glass epoxy PCBs)

单击下面可查看定价，库存，交付和生命周期等信息

[>>Willsemi\(韦尔半导体\)](#)